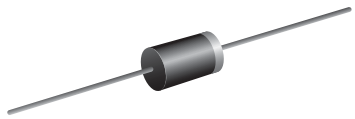
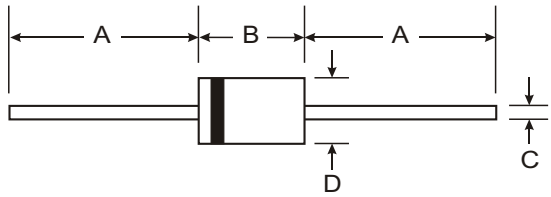
ERA15-01 – ERA15-10

PLASTIC SILICON RECTIFIER DIODES

VOLTAGE RANGE: 100 - 1000 V
CURRENT: 1.0 A





Features

- Diffused Junction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability

Mechanical Data

- Case: D O - 4 1
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.35 grams (approx.)
- Mounting Position: Any
- Marking: Type Number

RoHS COMPLIANT

DO-41		
Dim	**Min**	**Max**
A	25.40	—
B	4.06	5.21
C	0.71	0.864
D	2.00	2.72
All Dimensions in mm		

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	ERA15-01	ERA15-02	ERA15-04	ERA15 -06	ERA15-08	ERA15-10	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	100	200	400	600	800	1000	V
RMS Reverse Voltage	$V_{R(RMS)}$	70	140	280	420	560	700	V
Average Rectified Output Current (Note 1) @T_A = 75°C	I_O	1.0						A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	40						A
Forward Voltage @I_F = 1.0A	V_{FM}	1.0						V
Peak Reverse Current @T_A = 25°C At Rated DC Blocking Voltage @T_A = 100°C	I_{RM}	5.0 50						μA
Typical Junction Capacitance (Note 2)	C_j	15						pF
Typical Thermal Resistance Junction to Ambient (Note 1)	$R_{\theta JA}$	50						K/W
Operating Temperature Range	T_j	-65 to +125						°C
Storage Temperature Range	T_{STG}	-65 to +150						°C

Note: 1. Leads maintained at ambient temperature at a distance of 9.5mm from the case
2. Measured at 1.0 MHz and Applied Reverse Voltage of 4.0V D.C.

FIG.1 -- TYPICAL FORWARD CHARACTERISTIC

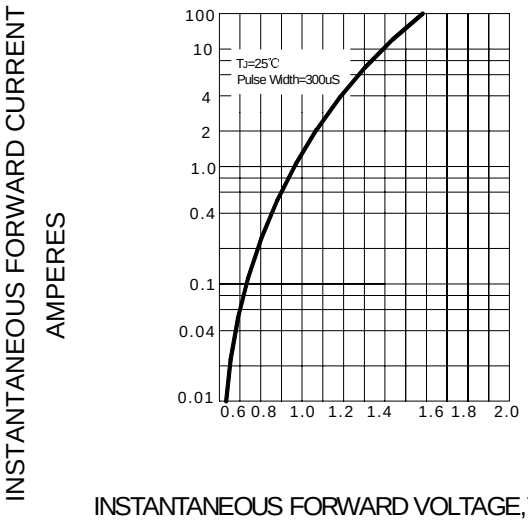


FIG.2 -- TYPICAL JUNCTION CAPACITANCE

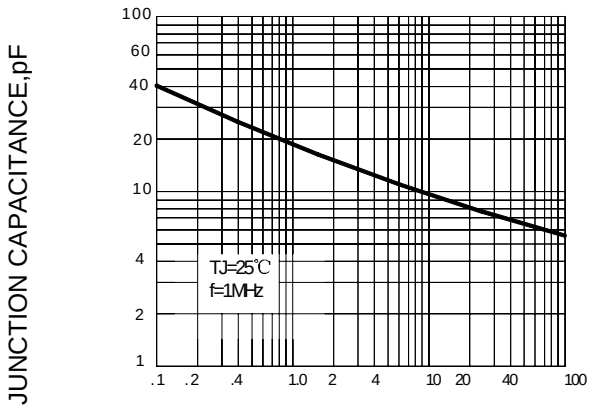


FIG.3 -- PEAK FORWARD SURGE CURRENT

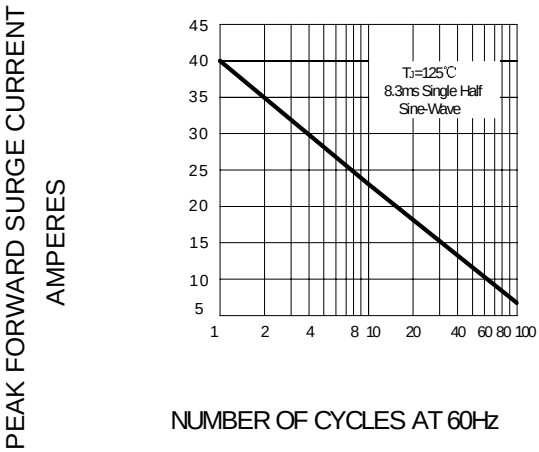


FIG.4 -- FORWARD DERATING CURVE